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MCU05N20

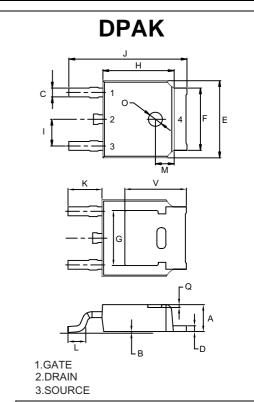
Features

- Fast switching
- Improved dv/dt capability
- Halogen free available upon request by adding suffix "-HF"
- · Excellent package for good heat dissipation
- Epoxy meets UL 94 V-0 flammability rating
- Moisture Sensitivity Level 1

Maximum Ratings @ 25°C Unless Otherwise Specified

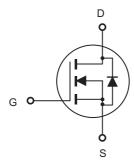
Symbol	Parameter	Rating	Unit	
V_{DS}	Drain-source Voltage	200	V	
I _D	Drain Current-Continuous Tc=25°C	5		
	Tc=100°C	3.24	А	
E _{AS}	Single Pulsed Avalanche Energy(note2)	125	mJ	
V_{GS}	Gate-source Voltage	±30	V	
I_{DM}	Pulsed Drain Current(note1)	20	Α	
R _{eJC}	Thermal Resistance Junction to Case	1.6	°C/W	
P _D	$ \begin{array}{ccc} \mbox{Power Dissipation} & \mbox{Tc=25^{\circ}C} \\ \mbox{Linear Derating Factor} & \mbox{Tc} > 25^{\circ}C \end{array} $	78 0.625	W W/°C	
dV/dt	Peak Diode Recovery Energy(note3)	5	V/ns	
TJ	Operating Junction Temperature	-55 to +150	°C	
T _{STG}	Storage Temperature	-55 to +150	$^{\circ}\mathbb{C}$	

N-Channel Enhancement Mode Field Effect Transistor



DIMENSIONS NOTE MIN MAX MIN MAX 0.087 0.094 2.20 0.000 0.005 0.00 0.026 0.034 0.66 0.86 0.018 0.023 0.46 0.264 6.70 5.10 5.46 0.236 6.00 0.244 6.20 0.086 0.094 2.18 М 0.043 1.30 0.051 1.10 0.00 0.012

Internal Block Diagram





Electrical Characteristics $T_c=25^{\circ}C$ unless otherwise specified

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
Off Charac	teristic					
V _{(BR)DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	200	-	-	V
$\triangle V_{(BR)DSS}$	Breakdown Voltage Temperature	Reference to 25℃,		0.05		V/°C
/△T _J	Coefficient	I _D = 250μA	-	0.25	,	V/ C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 200V, V _{GS} = 0V	-	-	1	μA
		$V_{DS} = 160V, T_{C} = 125^{\circ}C$	-	1	10	μA
I _{GSS}	Gate to Body Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 30V$	-	1	±100	nA
On Charac	teristics					
$V_{GS(th)}$	Gate Threshold Voltage note4	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1	1.9	3	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D = 2.5A	-	0.49	0.58	Ω
g FS	Forward Transconductance	$V_{DS} = 30V$, $I_D = 2.5A$	-	5.2	-	S
Dynamic C	Characteristics					
C _{iss}	Input Capacitance	V 25V V 0V	-	255	-	pF
Coss	Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$	-	30.2	-	pF
C _{rss}	Reverse Transfer Capacitance	f = 1.0MHz	-	2.3	-	pF
Qg	Total Gate Charge	VDD - 160V ID - 54	-	10.8	-	nC
Q _{gs}	Gate-Source Charge	VDD = 160V, ID = 5A,	-	1.7	-	nC
Q _{gd}	Gate-Drain("Miller") Charge	$V_{GS} = 10V$	-	3.1	-	nC
Switching	Characteristics					
t _{d(on)}	Turn-On Delay Time		-	7.33	-	ns
t _r	Turn-On Rise Time	$V_{DD} = 100V, I_D = 5A,$	-	10.7	-	ns
t _{d(off)}	Turn-Off Delay Time	RG = 10Ω, VGS = 10V	-	18.2	-	ns
t _f	Turn-Off Fall Time		-	11.9	-	ns
Drain-Soul	rce Diode Characteristics and Maximum I	Ratings				
Is	Maximum Continuous Drain to Source Diode Forward Current		-	-	5	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	20	Α
V _{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0V, I_{S} = 5A$	-	-	1.4	V
t _{rr}	Reverse Recovery Time	$V_{GS} = 0V, I_F = 5A,$	-	125.5	-	ns
Qrr	Reverse Recovery Charge	di/dt =100A/µs	-	357	-	nC

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. L = 10mH, $I_{AS} = 5A,~V_{DD} = 50V,~R_G = 25\Omega,~Starting~T_J = 25^{\circ}\!C$
- 3. $I_{SD} \le 5A$, di/dt $\le 200A/\mu s$, $V_{DD} \le B_{VDSS}$, Starting $T_J = 25^{\circ}C$
- 4. Pulse width ≤ 300µs; duty cycle ≤ 2%.



Typical Characteristics

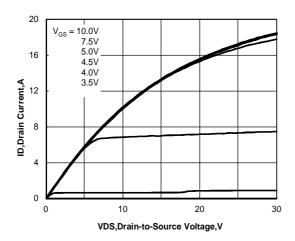


Figure 1. Output Characteristics

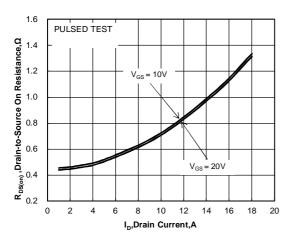
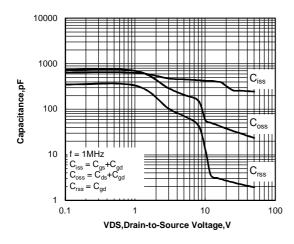


Figure 3. Drain-to-Source On Resistance vs.

Drain Current and Gate Voltage



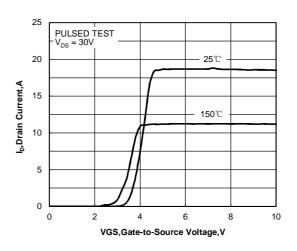


Figure 2. Transfer Characteristics

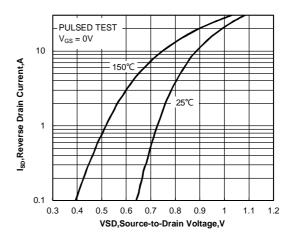
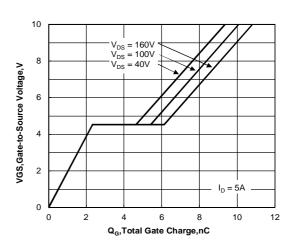


Figure 4. Body Diode Forward Voltage vs.

Source Current and Temperature





Ordering Information:

Device	Packing
Part Number-TP	Tape&Reel:2.5Kpcs/Reel

Note: Adding "-HF" suffix for halogen free, eg. Part Number-TP-HF

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